

Karen L Kavanagh

List of Publications by Year in descending order

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203
papers

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81900

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all docs

206
docs citations

206
times ranked

6592
citing authors

#	ARTICLE	IF	CITATIONS
1	Surface Plasmon Sensor Based on the Enhanced Light Transmission through Arrays of Nanoholes in Gold Films. <i>Langmuir</i> , 2004, 20, 4813-4815.	3.5	715
2	A New Generation of Sensors Based on Extraordinary Optical Transmission. <i>Accounts of Chemical Research</i> , 2008, 41, 1049-1057.	15.6	492
3	Generation of misfit dislocations in semiconductors. <i>Journal of Applied Physics</i> , 1987, 62, 4413-4420.	2.5	464
4	Strong Polarization in the Optical Transmission through Elliptical Nanohole Arrays. <i>Physical Review Letters</i> , 2004, 92, 037401.	7.8	439
5	Nanohole-Enhanced Raman Scattering. <i>Nano Letters</i> , 2004, 4, 2015-2018.	9.1	418
6	Luminescent Colloidal Silicon Suspensions from Porous Silicon. <i>Science</i> , 1992, 255, 66-68.	12.6	237
7	Asymmetries in dislocation densities, surface morphology, and strain of GaInAs/GaAs single heterolayers. <i>Journal of Applied Physics</i> , 1988, 64, 4843-4852.	2.5	208
8	Nonalloyed ohmic contacts to GaAs by solid-phase epitaxy of Ge. <i>Journal of Applied Physics</i> , 1987, 62, 942-947.	2.5	204
9	Enhanced Fluorescence from Arrays of Nanoholes in a Gold Film. <i>Journal of the American Chemical Society</i> , 2005, 127, 14936-14941.	13.7	203
10	Thin epitaxial Ge ¹¹¹ Si(111) films: Study and control of morphology. <i>Surface Science</i> , 1987, 191, 305-328.	1.9	164
11	Resonant optical transmission through hole arrays in metal films: physics and applications. <i>Laser and Photonics Reviews</i> , 2010, 4, 311-335.	8.7	150
12	Misfit dislocations in nanowire heterostructures. <i>Semiconductor Science and Technology</i> , 2010, 25, 024006.	2.0	149
13	Fermi-Level Pinning by Misfit Dislocations at GaAs Interfaces. <i>Physical Review Letters</i> , 1983, 51, 1783-1786.	7.8	132
14	Observation of quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells. <i>Applied Physics Letters</i> , 1999, 74, 2337-2339.	3.3	126
15	Lattice Compression from Conduction Electrons in Heavily Doped Si:As. <i>Physical Review Letters</i> , 1988, 61, 1748-1751.	7.8	112
16	Growth, branching, and kinking of molecular-beam epitaxial $\text{In}_{1-x}\text{Ga}_x\text{As}$ nanowires. <i>Applied Physics Letters</i> , 2003, 83, 3368-3370.	3.3	112
17	Effects of GaAs substrate misorientation on strain relaxation in $\text{In}_x\text{Ga}_{1-x}\text{As}$ films and multilayers. <i>Journal of Applied Physics</i> , 1998, 83, 5137-5149.	2.5	102
18	Apex-Enhanced Raman Spectroscopy Using Double-Hole Arrays in a Gold Film. <i>Journal of Physical Chemistry C</i> , 2007, 111, 2347-2350.	3.1	96

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19	Strain relaxation of compositionally graded In _x Ga _{1-x} As buffer layers for modulation-doped In _{0.3} Ga _{0.7} As/In _{0.29} Al _{0.71} As heterostructures. Applied Physics Letters, 1992, 60, 1129-1131.	3.3	95
20	Heteroepitaxial Growth of Vertical GaAs Nanowires on Si (111) Substrates by Metal-Organic Chemical Vapor Deposition. Nano Letters, 2008, 8, 3755-3760.	9.1	93
21	Structural and Room-Temperature Transport Properties of Zinc Blende and Wurtzite InAs Nanowires. Advanced Functional Materials, 2009, 19, 2102-2108.	14.9	86
22	Direct Measurement of Coherency Limits for Strain Relaxation in Heteroepitaxial Core/Shell Nanowires. Nano Letters, 2013, 13, 1869-1876.	9.1	80
23	Effects of rapid thermal annealing on GaInNAs/GaAs multiple quantum wells. Journal of Crystal Growth, 1999, 201-202, 419-422.	1.5	78
24	Enhancement of band edge luminescence in ZnSe nanowires. Journal of Applied Physics, 2006, 100, 084316.	2.5	78
25	Electron-Energy-Loss Scattering near a Single Misfit Dislocation at the GaAs/GaNAs Interface. Physical Review Letters, 1986, 57, 2729-2732.	7.8	75
26	Basis and Lattice Polarization Mechanisms for Light Transmission through Nanohole Arrays in a Metal Film. Nano Letters, 2005, 5, 1243-1246.	9.1	66
27	Surface Plasmon-Quantum Dot Coupling from Arrays of Nanoholes. Journal of Physical Chemistry B, 2006, 110, 8307-8313.	2.6	64
28	Silicon diffusion at polycrystalline-Si/GaAs interfaces. Applied Physics Letters, 1985, 47, 1208-1210.	3.3	59
29	Transport and strain relaxation in wurtzite InAs-GaAs core-shell heterowires. Applied Physics Letters, 2011, 98, .	3.3	57
30	Faster radial strain relaxation in InAs-GaAs core-shell heterowires. Journal of Applied Physics, 2012, 111, .	2.5	57
31	Lattice-strained heterojunction InGaAs/GaAs bipolar structures: Recombination properties and device performance. Journal of Applied Physics, 1987, 61, 1234-1236.	2.5	56
32	Lattice tilt and dislocations in compositionally step-graded buffer layers for mismatched InGaAs/GaAs heterointerfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 1820.	1.6	49
33	Growth-induced magnetic anisotropy and clustering in vapor-deposited Co-Pt alloy films. Physical Review B, 1999, 60, 12826-12836.	3.2	49
34	Ohmic contacts to GaAs using In/Pd metallization. Applied Physics Letters, 1987, 51, 326-327.	3.3	48
35	Probing the electrical transport properties of intrinsic InN nanowires. Applied Physics Letters, 2013, 102, .	3.3	48
36	Developing 1D nanostructure arrays for future nanophotonics. Nanoscale Research Letters, 2006, 1, 99-119.	5.7	46

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37	Porous silicon - what is responsible for the visible luminescence?. <i>Advanced Materials</i> , 1992, 4, 432-434.	21.0	45
38	Nanometer-resolved spatial variations in the Schottky barrier height of a Au/n-type GaAs diode. <i>Physical Review B</i> , 1994, 49, 16474-16479.	3.2	45
39	The interdiffusion of Si, P, and In at polysilicon/GaAs interfaces. <i>Journal of Applied Physics</i> , 1988, 64, 1845-1854.	2.5	40
40	Nanoscale Electrical and Structural Characterization of Gold/Alkyl Monolayer/Silicon Diode Junctions. <i>Journal of Physical Chemistry C</i> , 2008, 112, 9081-9088.	3.1	39
41	Geometric limits of coherent III-V core/shell nanowires. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	39
42	Gas-source molecular beam epitaxial growth and thermal annealing of GaInNAs/GaAs quantum wells. <i>Journal of Crystal Growth</i> , 2000, 208, 145-152.	1.5	38
43	Structure and photoluminescence of ZnSe nanostructures fabricated by vapor phase growth. <i>Journal of Applied Physics</i> , 2007, 101, 014326.	2.5	38
44	Relationship between surface morphology and strain relaxation during growth of InGaAs strained layers. <i>Applied Physics Letters</i> , 1995, 67, 3744-3746.	3.3	37
45	Correlation of anisotropic strain relaxation with substrate misorientation direction at InGaAs/GaAs(001) interfaces. <i>Applied Physics Letters</i> , 1995, 67, 344-346.	3.3	37
46	Twinning modulation in ZnSe nanowires. <i>Semiconductor Science and Technology</i> , 2007, 22, 175-178.	2.0	37
47	Molecular Orientation in Octanedithiol and Hexadecanethiol Monolayers on GaAs and Au Measured by Infrared Spectroscopic Ellipsometry. <i>Langmuir</i> , 2009, 25, 919-923.	3.5	37
48	Scanning spreading resistance microscopy current transport studies on doped III-V semiconductors. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 1682.	1.6	36
49	Defect studies of ZnSe nanowires. <i>Nanotechnology</i> , 2008, 19, 215715.	2.6	36
50	Ballistic Electron Emission Microscopy Studies of Au/Molecule/n-GaAs Diodes. <i>Journal of Physical Chemistry B</i> , 2005, 109, 6252-6256.	2.6	33
51	Field Dependent Transport Properties in InAs Nanowire Field Effect Transistors. <i>Nano Letters</i> , 2008, 8, 3114-3119.	9.1	33
52	Calibrated scanning spreading resistance microscopy profiling of carriers in III-V structures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 1662.	1.6	32
53	Anisotropic resistivity correlated with atomic ordering in p-type GaAsSb. <i>Applied Physics Letters</i> , 2001, 79, 2384-2386.	3.3	31
54	Growth of InAsSb/InAs MQWs on GaSb for mid-IR photodetector applications. <i>Journal of Crystal Growth</i> , 2009, 311, 3563-3567.	1.5	31

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55	Time dependent ballistic electron emission microscopy studies of a Au/(100)GaAs interface with a native oxide diffusion barrier. Applied Physics Letters, 1993, 62, 2965-2967.	3.3	30
56	Gas-source molecular beam epitaxial growth, characterization, and light-emitting diode application of In _x Ga _{1-x} P on GaP(100). Applied Physics Letters, 1993, 62, 2369-2371.	3.3	29
57	Rectifying characteristics of Te-doped GaAs nanowires. Applied Physics Letters, 2011, 99, 182102.	3.3	29
58	Multiple dislocation loops in linearly graded In _x Ga _{1-x} As (0 ≤ x ≤ 0.53) on GaAs and In _x Ga _{1-x} P (0 ≤ x ≤ 0.32) on GaP. Applied Physics Letters, 1993, 63, 500-502.	3.3	28
59	Lateral variation in the Schottky barrier height of Au/PtSi/(100)Si diodes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 2634.	1.6	26
60	Substrate effects on the ferroelectric properties of fine-grained BaTiO ₃ films. Journal of Applied Physics, 2003, 94, 5982-5989.	2.5	26
61	Study of 1/4-scale spatial variations in strain of a compositionally step-graded In _x Ga _{1-x} As/GaAs(001) heterostructure. Applied Physics Letters, 1995, 66, 869-871.	3.3	25
62	Improved Performance of Nanohole Surface Plasmon Resonance Sensors by the Integrated Response Method. IEEE Photonics Journal, 2011, 3, 441-449.	2.0	25
63	Reduction of Gold Penetration through Phenyl-Terminated Alkyl Monolayers on Silicon. Journal of Physical Chemistry C, 2012, 116, 17040-17047.	3.1	25
64	Aligned Co nanodiscs by electrodeposition on GaAs. Journal of Crystal Growth, 2006, 287, 514-517.	1.5	24
65	Metastable phase formation in the Au-Si system via ultrafast nanocalorimetry. Journal of Applied Physics, 2012, 111, .	2.5	24
66	Space-charge-limited current in nanowires. Journal of Applied Physics, 2017, 121, .	2.5	24
67	Hot-electron attenuation lengths in ultrathin magnetic films. Journal of Applied Physics, 2000, 87, 5164-5166.	2.5	23
68	Antimony segregation in GaAs-based multiple quantum well structures. Journal of Crystal Growth, 2003, 254, 28-34.	1.5	23
69	Preparation of ideal molecular junctions: depositing non-invasive gold contacts on molecularly modified silicon. Nanoscale, 2011, 3, 1434.	5.6	23
70	Direct Measurement of the Electrical Abruptness of a Nanowire p-n Junction. Nano Letters, 2016, 16, 3982-3988.	9.1	23
71	Anisotropic structural, electronic, and optical properties of InGaAs grown by molecular beam epitaxy on misoriented substrates. Applied Physics Letters, 1994, 65, 1424-1426.	3.3	22
72	Comparison of strain relaxation in InGaAsN and InGaAs thin films. Applied Physics Letters, 2002, 80, 4357-4359.	3.3	22

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73	Epitaxial Fe ²⁺ -GaAs via electrochemistry. Journal of Applied Physics, 2005, 98, 066103.	2.5	22
74	Growth and strain relaxation of GaAs and GaP nanowires with GaSb shells. Journal of Applied Physics, 2013, 113, 134309.	2.5	22
75	Modulation-doped In _{0.3} Ga _{0.7} As/In _{0.29} Al _{0.71} As heterostructures grown on GaAs by step grading. Semiconductor Science and Technology, 1992, 7, 601-603.	2.0	21
76	Lattice strain from substitutional Ga and from holes in heavily doped Si:Ga. Physical Review B, 1992, 45, 3323-3331.	3.2	21
77	Planar Ge/Pd and alloyed Au-Ge-Ni ohmic contacts to Al _x Ga _{1-x} As (0 ≤ x ≤ 0.3). Applied Physics Letters, 1989, 54, 721-723.	3.3	19
78	Quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells grown by gas-source molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1649.	1.6	19
79	Structural and magnetic properties of NiMnSb/InGaAs/InP(001). Journal of Applied Physics, 2005, 97, 073906.	2.5	19
80	Epitaxial Bi ³⁺ -GaAs diodes via electrodeposition. Journal of Vacuum Science & Technology B, 2006, 24, 2138.	1.3	19
81	High-resolution X-ray diffraction of InAlAs/InP superlattices grown by gas source molecular beam epitaxy. Applied Physics Letters, 1991, 58, 1530-1532.	3.3	17
82	Epitaxial Bi ³⁺ -GaAs(111) diodes via electrodeposition. Applied Physics Letters, 2006, 88, 022102.	3.3	17
83	The Polycrystalline-Si Contact to GaAs. Journal of the Electrochemical Society, 1986, 133, 1176-1179.	2.9	15
84	Optical detection of misfit dislocation-induced deep levels at InGaAs/GaAs heterojunctions. Applied Physics Letters, 1994, 64, 3572-3574.	3.3	15
85	Au/ZnSe contacts characterized by ballistic electron emission microscopy. Journal of Applied Physics, 1996, 79, 1532-1535.	2.5	15
86	Role of interface microstructure in rectifying metal/semiconductor contacts: Ballistic electron emission observations correlated to microstructure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1238.	1.6	15
87	Large-Area Low-Cost Flexible Plastic Nanohole Arrays for Integrated Bio-Chemical Sensing. IEEE Sensors Journal, 2013, 13, 3982-3990.	4.7	15
88	Relaxation-induced polarized luminescence from In _x Ga _{1-x} As films grown on GaAs(001). Physical Review B, 1995, 51, 5033-5037.	3.2	14
89	p-type doping of GaAs nanowires using carbon. Journal of Applied Physics, 2012, 112, 094323.	2.5	14
90	Lithography-Free Fabrication of Core-Shell GaAs Nanowire Tunnel Diodes. Nano Letters, 2015, 15, 5408-5413.	9.1	14

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91	Correlation of buffer strain relaxation modes with transport properties of two-dimensional electron gases. <i>Journal of Applied Physics</i> , 1996, 80, 6849-6854.	2.5	13
92	Faceting transition in epitaxial growth of dilute GaNAs films on GaAs. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 1417.	1.6	12
93	Residual Stress, Defects, and Electrical Properties of Epitaxial Copper Growth on GaAs. <i>Journal of the Electrochemical Society</i> , 2009, 156, D138.	2.9	12
94	Electrodeposition, characterization and morphological investigations of NiFe/Cu multilayers prepared by pulsed galvanostatic, dual bath technique. <i>Materials Characterization</i> , 2011, 62, 204-210.	4.4	12
95	Controlled axial and radial Te-doping of GaAs nanowires. <i>Journal of Applied Physics</i> , 2012, 112, 054324.	2.5	12
96	Tensile strain relaxation in GaN _x P _{1-x} (x ≈ 0.1) grown by chemical beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 2952.	1.6	11
97	Ballistic electron and photocurrent transport in Au-molecular layer-GaAs diodes. <i>Journal of Applied Physics</i> , 2007, 102, .	2.5	11
98	Effect of Bi surfactant on atomic ordering of GaAsSb. <i>Applied Physics Letters</i> , 2004, 85, 5589-5591.	3.3	10
99	Long-lasting flexible organic solar cells stored and tested entirely in air. <i>Applied Physics Letters</i> , 2011, 99, 263305.	3.3	10
100	Role of Hydrogen Evolution during Epitaxial Electrodeposition of Fe on GaAs. <i>Journal of the Electrochemical Society</i> , 2018, 165, H3076-H3079.	2.9	10
101	Growth of h-BN on copper (110) in a LEEM. <i>Surface Science</i> , 2018, 669, 133-139.	1.9	10
102	Hole confinement and low-frequency noise in SiGe pFETs on silicon-on-sapphire. <i>IEEE Electron Device Letters</i> , 1999, 20, 173-175.	3.9	9
103	The growth of SiGe on sapphire using rapid thermal chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2001, 222, 20-28.	1.5	9
104	Effects of capillary forces on copper dielectric interfacial void evolution. <i>Applied Physics Letters</i> , 2004, 84, 5201-5203.	3.3	9
105	Planar defects and phase transformation in ZnSe nanosaws. <i>Journal of Materials Science: Materials in Electronics</i> , 2006, 17, 1065-1070.	2.2	9
106	Epitaxial Fe _x Ni _{1-x} Thin Film Contacts to GaAs via Electrochemistry. <i>Journal of the Electrochemical Society</i> , 2008, 155, H841.	2.9	9
107	Detecting Antibodies Secreted by Trapped Cells Using Extraordinary Optical Transmission. <i>IEEE Sensors Journal</i> , 2011, 11, 2732-2739.	4.7	9
108	Si diffusion and segregation in low-temperature grown GaAs. <i>Applied Physics Letters</i> , 1993, 62, 286-288.	3.3	8

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109	Comparison of Au contacts to Si, GaAs, In _x Ga _{1-x} P, and ZnSe measured by ballistic electron emission microscopy. <i>Materials Chemistry and Physics</i> , 1996, 46, 224-229.	4.0	8
110	Modulation-doped In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As heterostructures grown on GaAs substrates using step-graded In _x Ga _{1-x} As buffers. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 3035.	1.6	8
111	Wavelength-Invariant Resist Composed of Bimetallic Layers. <i>Materials Research Society Symposia Proceedings</i> , 2002, 745, 381.	0.1	8
112	Plasmonic sensors based on nano-holes: technology and integration. <i>Proceedings of SPIE</i> , 2008, , .	0.8	8
113	Aligned cuboid iron nanoparticles by epitaxial electrodeposition. <i>Nanoscale</i> , 2017, 9, 5315-5322.	5.6	8
114	Electrical properties of lightly Ga-doped ZnO nanowires. <i>Semiconductor Science and Technology</i> , 2017, 32, 125010.	2.0	8
115	Room-temperature electrosynthesis of carbonaceous fibers. <i>Advanced Materials</i> , 1995, 7, 398-401.	21.0	7
116	X-Ray Diffuse Scattering from Misfit Dislocation at Buried Interface. <i>Materials Research Society Symposia Proceedings</i> , 2001, 673, 1.	0.1	7
117	Strain relaxation by ~100% misfit dislocations in dilute nitride In _x Ga _{1-x} As _{1-y} Ny/GaAs quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 2849-2857.	1.8	7
118	Lateral spin injection and detection through electrodeposited Fe/GaAs contacts. <i>Semiconductor Science and Technology</i> , 2013, 28, 035003.	2.0	7
119	Anisotropic Surface Roughness in Strain Relaxed In _{0.40} Ga _{0.60} As on GaAs with a Step-Graded In _x Ga _{1-x} As Buffer Layer. <i>Materials Research Society Symposia Proceedings</i> , 1993, 312, 107.	0.1	6
120	Interfacial scattering of hot electrons in ultrathin Au/Co films. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000, 18, 2047.	1.6	6
121	Au-Ag and Au-Pd molecular contacts to GaAs. <i>Journal of Vacuum Science & Technology B</i> , 2008, 26, 1597-1601.	1.3	6
122	Atomic ordering in GaAsSb (001) grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2009, 311, 4391-4397.	1.5	6
123	Recycling gold nanohole arrays. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2014, 32, .	2.1	6
124	Interfacial reactions at Fe/topological insulator spin contacts. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, 04F105.	1.2	6
125	Structural and electrical characteristics of microcrystalline silicon prepared by hot-wire chemical vapor deposition using a graphite filament. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2007, 25, 464-467.	2.1	5
126	Transparent conducting indium bismuth oxide. <i>Thin Solid Films</i> , 2007, 515, 3760-3765.	1.8	5

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127	Improved chemical and electrical stability of gold silicon contacts via epitaxial electrodeposition. Journal of Applied Physics, 2013, 113, 063708.	2.5	5
128	Title is missing!. Journal of Medical and Biological Engineering, 2011, 31, 121.	1.8	5
129	Cw laser crystallization of glow discharge a-Si:H on glass substrates. Journal of Electronic Materials, 1982, 11, 303-320.	2.2	4
130	The Diffusion of Phosphorus and Indium into Gallium Arsenide from Polycrystalline-Silicon. Materials Research Society Symposia Proceedings, 1986, 77, 785.	0.1	4
131	Oxidation induced AlAs/GaAs superlattice disordering. Applied Physics Letters, 1992, 60, 1235-1237.	3.3	4
132	Beem Investigation of Oxide and Sulfide Passivated GaAs. Materials Research Society Symposia Proceedings, 1992, 281, 653.	0.1	4
133	Dislocation-Induced deep level states in In _{0.08} Ga _{0.92} As/GaAs heterostructures. Journal of Electronic Materials, 1994, 23, 929-933.	2.2	4
134	Evolution of interface voids under current and temperature stress in integrated circuit metallization. Metals and Materials International, 2004, 10, 411-415.	3.4	4
135	Nanoholes in metals with applications to sensors and spectroscopy. International Journal of Nanotechnology, 2008, 5, 1058.	0.2	4
136	Sensing of antibodies secreted by microfluidically trapped cells via extraordinary optical transmission through nanohole arrays. , 2010, , .		4
137	Effect of annealing on the structural and optical properties of heavily carbon-doped ZnO. Semiconductor Science and Technology, 2010, 25, 045023.	2.0	4
138	Electrical characterization of Si/InN nanowire heterojunctions. Semiconductor Science and Technology, 2018, 33, 015008.	2.0	4
139	Three-Dimensional Imaging of Beam-Induced Biasing of InP/GaInP Tunnel Diodes. Nano Letters, 2019, 19, 3490-3497.	9.1	4
140	Axial EBIC oscillations at core/shell GaAs/Fe nanowire contacts. Nanotechnology, 2019, 30, 025701.	2.6	4
141	Three-Dimensional Conductive Fingerprint Phantoms Made of Ethylene-Vinyl Acetate/Graphene Nanocomposite for Evaluating Smartphone Scanners. ACS Applied Electronic Materials, 2021, 3, 2097-2105.	4.3	4
142	<title>Control of surface morphology and strain relaxation in InGaAs grown on GaAs using a step-graded buffer</title>. , 1994, 2140, 179.		3
143	Microstructure of ordered nanodomains induced by Bi surfactant in OMVPE-grown GaAsSb. Journal of Crystal Growth, 2006, 287, 541-544.	1.5	3
144	Characterization of solution-bonded GaAs/InGaAs/GaAs features on GaAs. Semiconductor Science and Technology, 2014, 29, 075009.	2.0	3

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145	Regrowth mechanism for oxide isolation of GaAs nanowires. <i>Nanotechnology</i> , 2017, 28, 385302.	2.6	3
146	Measuring Surface Energies of GaAs (100) and Si (100) by Three Liquid Contact Angle Analysis (3LCAA) for Heterogeneous Nano-Bonding TM . <i>MRS Advances</i> , 2018, 3, 3403-3411.	0.9	3
147	A New Technique for Magnetic Nanoparticle Imaging Using Magnetoencephalography Frequency Data. <i>IFMBE Proceedings</i> , 2010, , 443-446.	0.3	3
148	Rotational epitaxy of h-BN ^Å on Cu (110). <i>Surface Science</i> , 2022, 721, 122080.	1.9	3
149	Luminescent Colloidal Si Suspensions from Porous Si. <i>Materials Research Society Symposia Proceedings</i> , 1991, 256, 131.	0.1	2
150	Strain relaxation induced deep levels in In ^{1^Å} xGa ^x As thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1994, 12, 1050-1053.	2.1	2
151	Lateral Variation in the Schottky Barrier Height and Observation of Critical Lengths at Au/PtSi/(100)Si and Au/(100)GaAs Diodes. <i>Materials Research Society Symposia Proceedings</i> , 1994, 337, 319.	0.1	2
152	Beem and UHV-TEM Studies of PtSi/Si(001). <i>Materials Research Society Symposia Proceedings</i> , 1995, 402, 461.	0.1	2
153	Influence of GaAs(001) substrate misorientation towards {111} on the optical properties of In ^x Ga ^{1^Å} xAs/GaAs. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1995, 13, 1766.	1.6	2
154	Analysis Of Sige Fet Device Structures On Silicon-on-sapphire Substrates by X-Ray Diffraction. <i>Materials Research Society Symposia Proceedings</i> , 1998, 533, 55.	0.1	2
155	Temporary extrusion failures in accelerated lifetime tests of copper interconnects. <i>IEEE Electron Device Letters</i> , 2005, 26, 622-624.	3.9	2
156	SU-8 polymer enclosed microchannels with interconnect and nanohole arrays as an optical detection device for biospecies. , 2008, 2008, 5652-5.		2
157	Inhomogeneous magnetization processes in electrodeposited iron thin films on GaAs. <i>Journal of Applied Physics</i> , 2009, 105, .	2.5	2
158	Insights into semiconductor nanowire conductivity using electrodeposition. <i>Semiconductor Science and Technology</i> , 2012, 27, 105020.	2.0	2
159	Hanle measurements of electrodeposited Fe/GaAs spin tunnel contacts. <i>Journal of Applied Physics</i> , 2014, 115, 123709.	2.5	2
160	Abrupt degenerately-doped silicon nanowire tunnel junctions. <i>Nanotechnology</i> , 2020, 31, 415708.	2.6	2
161	Homogeneous Strain Relaxation and Mosaic Spread in IngaAs/GaAs Heterostructures Using Triple Axis Diffractometry. , 1995, , 221-226.		2
162	RBS and TEM Analysis of Ta Silicides on GaAs. <i>Materials Research Society Symposia Proceedings</i> , 1983, 25, 143.	0.1	1

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163	Preparation of Cross Sectional TEM Samples Using Lithographic Techniques and Reactive Ion Etching. Materials Research Society Symposia Proceedings, 1990, 199, 43.	0.1	1
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